

isc Silicon NPN Power Transistor

BD797

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 60V(\text{Min.})$
- Low Saturation Voltage
- Complement to Type BD798

APPLICATIONS

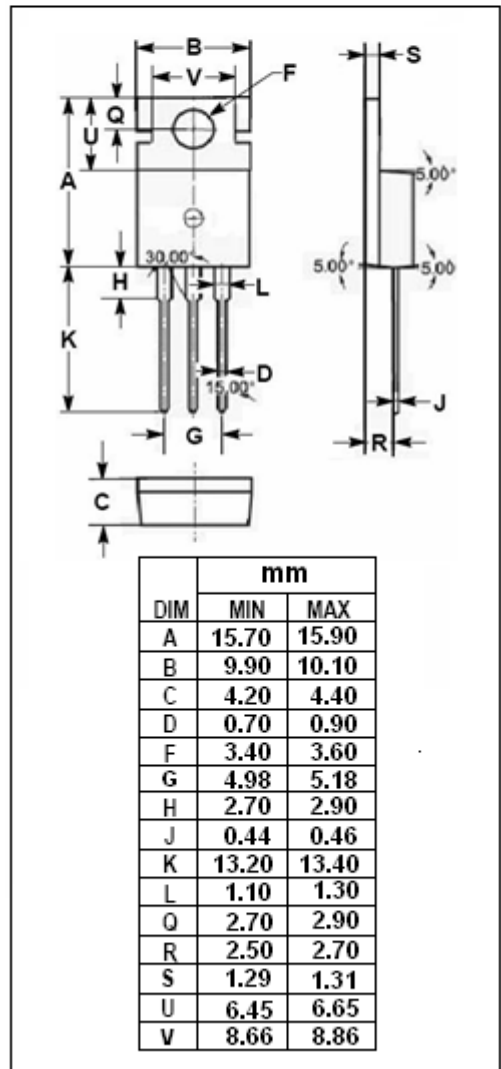
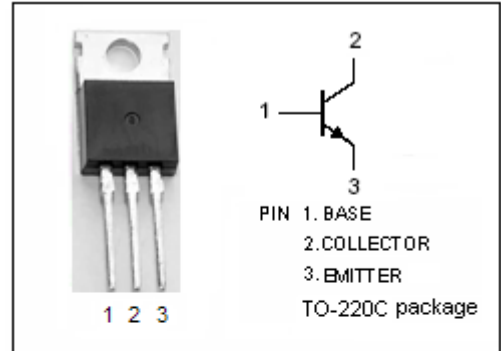
- Designed for a wide variety of medium-power switching and amplifier applications , such as series and shunt regulators and driver and output stages of high-fidelity amplifiers.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	8	A
I_B	Base Current-Continuous	3	A
P_C	Collector Power Dissipation $T_C=25^\circ\text{C}$	65	W
T_j	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Ttemperature Range	-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.92	$^\circ\text{C/W}$



isc Silicon NPN Power Transistor**BD797****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C= 100\text{mA}; I_B= 0$	60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C= 3\text{A}; I_B= 0.3\text{A}$			1	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C= 3\text{A}; V_{CE}= 2\text{V}$			1.6	V
I_{CBO}	Collector Cutoff Current	$V_{CB}= 60\text{V}; I_E= 0$			0.1	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}= 5\text{V}; I_C= 0$			1	mA
h_{FE-1}	DC Current Gain	$I_C= 1\text{A}; V_{CE}= 2\text{V}$	40			
h_{FE-2}	DC Current Gain	$I_C= 3\text{A}; V_{CE}= 2\text{V}$	25			
f_T	Current-Gain—Bandwidth Product	$I_C= 0.25\text{A}; V_{CE}= 10\text{V}, f_{test}= 1\text{MHz}$	3			MHz